

ABSTRACT

A method of manufacturing a magnetoresistance effect device, including: forming a first ferromagnetic body, a nonmagnetic dielectric layer on the first ferromagnetic body, and a second ferromagnetic body on the nonmagnetic dielectric layer; etching part of an external region of a predetermined ferromagnetic tunnel junction region using a first linear mask pattern which is traversing the predetermined ferromagnetic tunnel junction region; and etching another part of the external region of the predetermined ferromagnetic tunnel junction region using a second linear mask pattern which is traversing the predetermined ferromagnetic tunnel junction region and intersecting with the first linear mask pattern.